# **Silicon Power Transistors**

The MJ21193 (PNP) and MJ21194 (NPN) utilize Perforated Emitter technology and are specifically designed for high power audio output, disk head positioners and linear applications.

#### **Features**

- Total Harmonic Distortion Characterized
- High DC Current Gain
- Excellent Gain Linearity
- High SOA
- These Devices are Pb-Free and are RoHS Compliant\*

#### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	$V_{CEO}$	250	Vdc
Collector-Base Voltage	V <sub>CBO</sub>	400	Vdc
Emitter-Base Voltage	V <sub>EBO</sub>	5	Vdc
Collector-Emitter Voltage - 1.5 V	$V_{CEX}$	400	Vdc
Collector Current - Continuous	Ic	16	Adc
Collector Current – Peak (Note 1)	I <sub>CM</sub>	30	Adc
Base Current - Continuous	Ι <sub>Β</sub>	5	Adc
Total Power Dissipation @ T <sub>C</sub> = 25°C Derate Above 25°C	P <sub>D</sub>	250 1.43	W W/°C
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	- 65 to +200	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Pulse Test: Pulse Width = 5 μs, Duty Cycle ≤10%. (continued)

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	0.7	°C/W

1

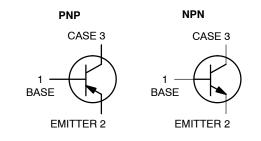


# ON Semiconductor®

http://onsemi.com

# 16 AMP COMPLEMENTARY SILICON POWER TRANSISTORS 250 VOLTS, 250 WATTS

#### **SCHEMATIC**









MJ2119x = Device Code

x = 3 or 4

G = Pb-Free Package A = Assembly Location

YY = Year WW = Work Week MEX = Country of Origin

#### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
MJ21193G	TO-3 (Pb-Free)	100 Units / Tray
MJ21194G	TO-3 (Pb-Free)	100 Units / Tray

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

<sup>\*</sup>For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

# **ELECTRICAL CHARACTERISTICS** (T<sub>C</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Sustaining Voltage (I <sub>C</sub> = 100 mAdc, I <sub>B</sub> = 0)	V <sub>CEO(sus)</sub>	250	-	_	Vdc
Collector Cutoff Current (V <sub>CE</sub> = 200 Vdc, I <sub>B</sub> = 0)	I <sub>CEO</sub>	-	-	100	μAdc
Emitter Cutoff Current $(V_{CE} = 5 \text{ Vdc}, I_C = 0)$	I <sub>EBO</sub>	-	-	100	μAdc
Collector Cutoff Current (V <sub>CE</sub> = 250 Vdc, V <sub>BE(off)</sub> = 1.5 Vdc)	I <sub>CEX</sub>	-		100	μAdc
SECOND BREAKDOWN	•				
Second Breakdown Collector Current with Base Forward Biased (V <sub>CE</sub> = 50 Vdc, t = 1 s (non-repetitive) (V <sub>CE</sub> = 80 Vdc, t = 1 s (non-repetitive)	I <sub>S/b</sub>	5 2.5	- -	_ _	Adc
ON CHARACTERISTICS					
DC Current Gain ( $I_C = 8$ Adc, $V_{CE} = 5$ Vdc) ( $I_C = 16$ Adc, $I_B = 5$ Adc)	h <sub>FE</sub>	25 8	_ _	75	
Base–Emitter On Voltage (I <sub>C</sub> = 8 Adc, V <sub>CE</sub> = 5 Vdc)	V <sub>BE(on)</sub>	-	-	2.2	Vdc
Collector–Emitter Saturation Voltage ( $I_C = 8$ Adc, $I_B = 0.8$ Adc) ( $I_C = 16$ Adc, $I_B = 3.2$ Adc)	V <sub>CE(sat)</sub>	- -	_ _	1.4 4	Vdc
DYNAMIC CHARACTERISTICS		·			
Total Harmonic Distortion at the Output  V <sub>RMS</sub> = 28.3 V, f = 1 kHz, P <sub>LOAD</sub> = 100 W <sub>RMS</sub> h <sub>FE</sub> unmatched	T <sub>HD</sub>	_	0.8	_	%
(Matched pair $h_{FE}$ = 50 @ 5 A/5 V) $h_{FE}$ matched		-	0.08	_	
Current Gain Bandwidth Product (I <sub>C</sub> = 1 Adc, V <sub>CE</sub> = 10 Vdc, f <sub>test</sub> = 1 MHz)	f <sub>T</sub>	4	_	_	MHz
Output Capacitance (V <sub>CB</sub> = 10 Vdc, I <sub>E</sub> = 0, f <sub>test</sub> = 1 MHz)	C <sub>ob</sub>	-	-	500	pF

NOTE: Pulse Test: Pulse Width = 300 µs, Duty Cycle ≤2%

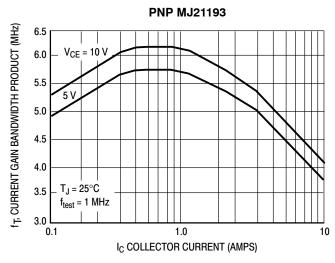


Figure 1. Typical Current Gain Bandwidth Product

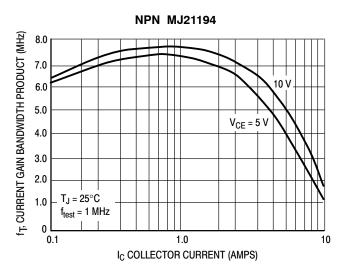


Figure 2. Typical Current Gain Bandwidth Product

#### **TYPICAL CHARACTERISTICS**

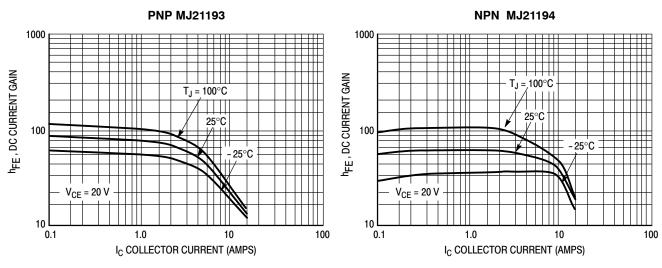


Figure 3. DC Current Gain, V<sub>CE</sub> = 20 V

Figure 4. DC Current Gain, V<sub>CE</sub> = 20 V

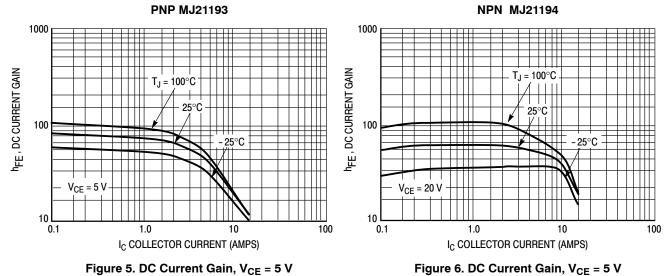


Figure 5. DC Current Gain, V<sub>CE</sub> = 5 V

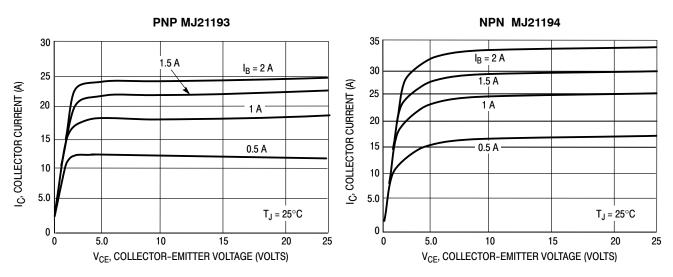


Figure 7. Typical Output Characteristics

Figure 8. Typical Output Characteristics

#### TYPICAL CHARACTERISTICS

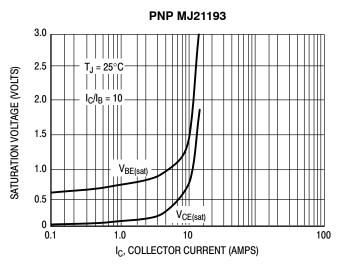


Figure 9. Typical Saturation Voltages

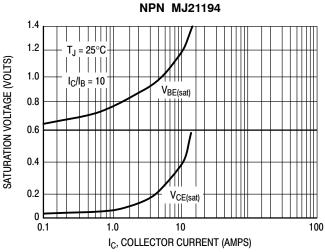


Figure 10. Typical Saturation Voltages

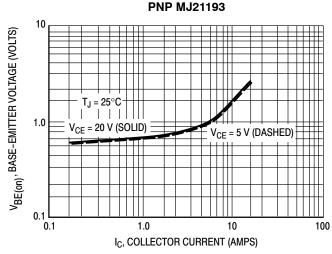


Figure 11. Typical Base-Emitter Voltage

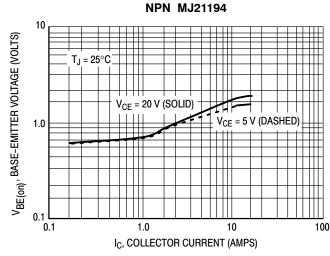


Figure 12. Typical Base-Emitter Voltage

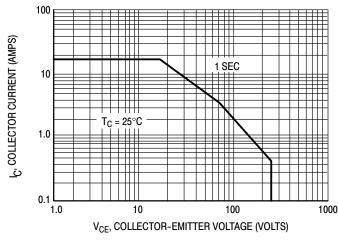


Figure 13. Active Region Safe Operating Area

There are two limitations on the power handling ability of a transistor; average junction temperature and secondary breakdown. Safe operating area curves indicate  $I_C - V_{CE}$  limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 13 is based on  $T_{J(pk)} = 200^{\circ}\mathrm{C}$ ;  $T_{C}$  is variable depending on conditions. At high case temperatures, thermal limitations will reduce the power than can be handled to values less than the limitations imposed by second breakdown.

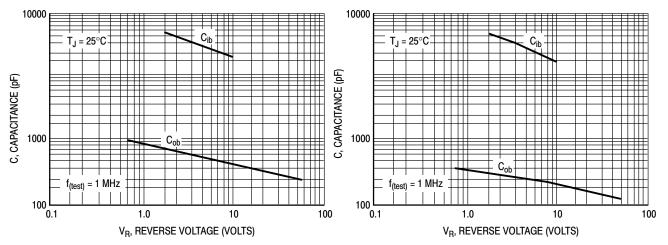


Figure 14. MJ21193 Typical Capacitance

Figure 15. MJ21194 Typical Capacitance

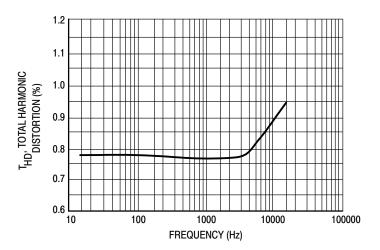


Figure 16. Typical Total Harmonic Distortion

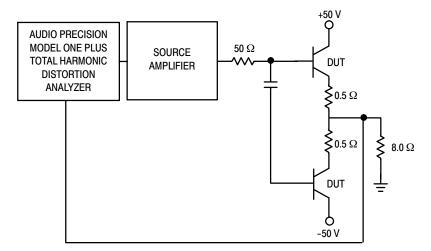
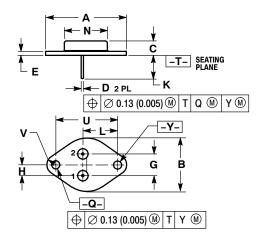


Figure 17. Total Harmonic Distortion Test Circuit

#### PACKAGE DIMENSIONS

## TO-204AA (TO-3)

**CASE 1-07** ISSUF 7



#### NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI
- Y14.5M, 1982.
  2. CONTROLLING DIMENSION: INCH.
- ALL RULES AND NOTES ASSOCIATED WITH REFERENCED TO-204AA OUTLINE SHALL APPLY.

	INCHES		MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
Α	1.550 REF		39.37	REF	
В		1.050		26.67	
С	0.250	0.335	6.35	8.51	
D	0.038	0.043	0.97	1.09	
E	0.055	0.070	1.40	1.77	
G	0.430	BSC	10.92	BSC	
Н	0.215 BSC		5.46 BSC		
K	0.440	0.480	11.18	12.19	
L	0.665	BSC	16.89 BSC		
N		0.830		21.08	
ø	0.151	0.165	3.84	4.19	
U	1.187	BSC	30.15 BSC		
٧	0.131	0.188	3.33	4.77	

PIN 1. BASE 2. EMITTER CASE: COLLECTOR

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